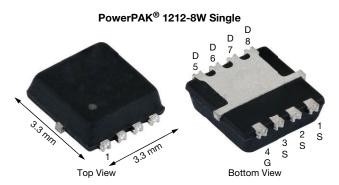


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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET



Marking Code: Q037

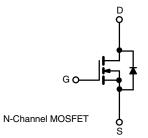
| PRODUCT SUMMARY | | | |
|--|------------------|--|--|
| V _{DS} (V) | 60 | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$ | 0.023 | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$ | 0.028 | | |
| I _D (A) | 18 | | |
| Configuration | Single | | |
| Package | PowerPAK 1212-8W | | |

FEATURES

- TrenchFET® power MOSFET
- Low thermal resistance PowerPAK® 1212-8 package with 1.07 mm profile
- PWM optimized
- 100 % R_a and UIS tested
- AEC-Q101 qualified
- · Wettable flank terminals
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>



ROHS COMPLIANT HALOGEN FREE



| PARAMETER | | SYMBOL | LIMIT | UNIT | |
|--|-------------------------|-----------------------------------|-------------|------|--|
| Drain-source voltage | | V _{DS} | 60 | V | |
| Gate-source voltage | | V_{GS} | ± 20 | V | |
| Continuous drain current ^a | T _C = 25 °C | - I _D | 18 | | |
| | T _C = 125 °C | | 18 | | |
| Continuous source current (diode conduction) a | | I _S | 18 | А | |
| Pulsed drain current ^b | | | 72 | | |
| Single pulse avalanche current | L = 0.1 mH | I _{AS} | 20 | | |
| Single pulse avalanche energy | L=0.11IIII | E _{AS} | 16 | mJ | |
| Maximum power dissipation ^b | T _C = 25 °C | P _D | 62 | - w | |
| | T _C = 125 °C | | 20 | | |
| Operating junction and storage temperature range | | T _J , T _{stg} | -55 to +175 | °C | |
| Soldering recommendations (peak temperature) d | | - | 260 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|----------------------------|-------------|------------|-------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Junction-to-ambient | PCB mount c | R_{thJA} | 81 | °C/W | |
| Junction-to-case (drain) | | R_{thJC} | 2.4 | | |

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2 \,\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



Vishay Siliconix

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|---|---------------------|--|---|------|-------|-------|------|
| Static | - | | | | | L | l |
| Drain-source breakdown voltage | V _{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | | 60 | - | - | V |
| Gate-source threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ | | 1.5 | 2 | 2.5 | |
| Gate-source leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | - | - | ± 100 | nA |
| Zero gate voltage drain current | | $V_{GS} = 0 V$ | V _{DS} = 60 V | - | - | 1 | μΑ |
| | I _{DSS} | V _{GS} = 0 V | V _{DS} = 60 V, T _J = 125 °C | - | - | 50 | |
| | | $V_{GS} = 0 V$ | V _{DS} = 60 V, T _J = 175 °C | =. | - | 150 | |
| On-state drain current a | I _{D(on)} | V _{GS} = 10 V | $V_{DS} \ge 5 V$ | 20 | - | - | Α |
| Drain-source on-state resistance ^a | | V _{GS} = 10 V | I _D = 8.7 A | - | 0.016 | 0.023 | Ω |
| | Ь | V _{GS} = 10 V | I _D = 8.7 A, T _J = 125 °C | =. | - | 0.039 | |
| | R _{DS(on)} | V _{GS} = 10 V | I _D = 8.7 A, T _J = 175 °C | =. | - | 0.050 | |
| | | V _{GS} = 4.5 V | I _D = 8.7 A | - | 0.019 | 0.028 | |
| Forward transconductance b | 9 _{fs} | V _{DS} : | = 15 V, I _D = 8.7 A | =. | 50 | =. | S |
| Dynamic ^b | | | | | | | |
| Input capacitance | C _{iss} | | V _{DS} = 30 V, f = 1 MHz | =. | 1275 | 1590 | pF |
| Output capacitance | C _{oss} | $V_{GS} = 0 V$ | | - | 112 | 140 | |
| Reverse transfer capacitance | C _{rss} | | | =. | 42 | 52 | |
| Total gate charge ^c | Qg | | V _{GS} = 10 V V _{DS} = 30 V, I _D = 8.7 A | - | 19 | 25 | nC |
| Gate-source charge ^c | Q_{gs} | $V_{GS} = 10 \text{ V}$ | | =. | 2.6 | - | |
| Gate-drain charge ^c | Q_{gd} | 1 | | =. | 3.6 | - | |
| Gate resistance | R _g | f = 1 MHz | | 0.6 | 1.12 | 1.6 | Ω |
| Turn-on delay time ^c | t _{d(on)} | | | - | 8 | 10 | |
| Rise time ^c | t _r | $V_{DD} = 30 \text{ V}, \text{ R}_{L} = 30 \Omega$ $I_{D} \cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$ | | - | 13 | 16 | ns |
| Turn-off delay time ^c | t _{d(off)} | | | - | 22 | 26 | |
| Fall time ^c | t _f | | | =. | 15 | 18 | |
| Source-Drain Diode Ratings and Char | acteristics b | | | | | | |
| Pulsed current ^a | I _{SM} | | | =. | - | 72 | Α |
| Forward voltage | V_{SD} | I _F = 8.7 A, V _{GS} = 0 V | | - | 0.8 | 1.2 | V |

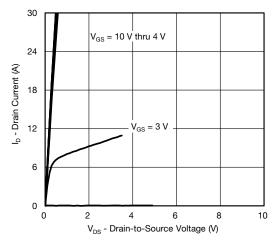
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

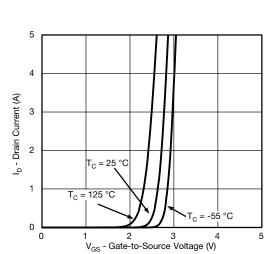
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



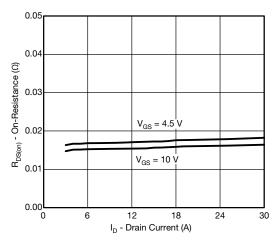
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



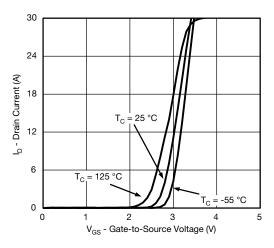
Output Characteristics



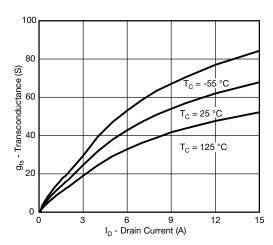
Transfer Characteristics



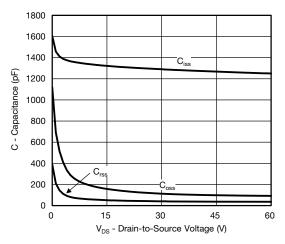
On-Resistance vs. Drain Current



Transfer Characteristics



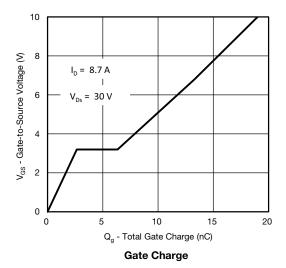
Transconductance

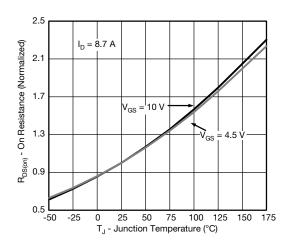


Capacitance

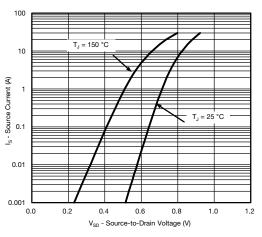


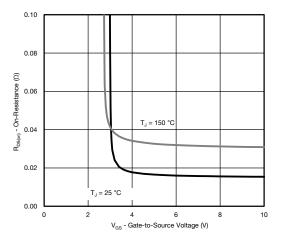
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





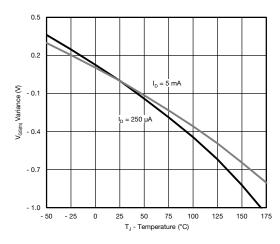
On-Resistance vs. Junction Temperature

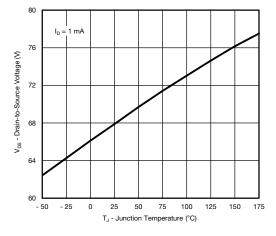




Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage



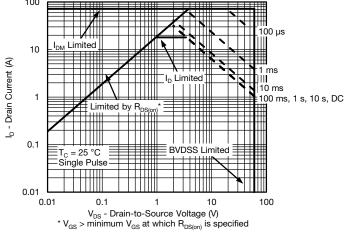


Threshold Voltage

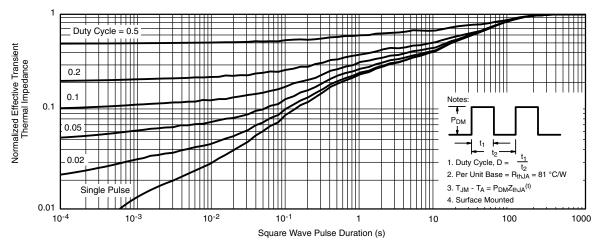
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



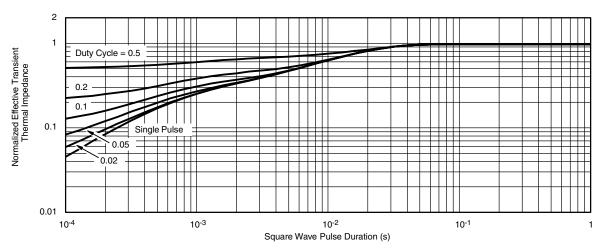
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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